



### **Product Summary**

BV <sub>DSS</sub>	Rds(on) Max	I <sub>D</sub> Max T <sub>A</sub> = +25°C
60V	6Ω @ V <sub>GS</sub> = 5V	220mA

# **Description and Applications**

This MOSFET has been designed to minimize the on-state resistance ( $R_{DS(ON)}$ ) yet maintain superior switching performance, making it ideal for high efficiency power management applications.

- Motor Control
- Power Management Functions

## Features and Benefits

- N-Channel MOSFET
- Low On-Resistance
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Small Surface Mount Package
- ESD Protected Gate, 1.2kV HBM, 1kV CDM
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)

N-CHANNEL ENHANCEMENT MODE MOSFET

- Halogen and Antimony Free. "Green" Device (Note 3)
- For automotive applications requiring specific change control (i.e.: parts qualified to AEC-Q100/101/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please refer to the related automotive grade (Qsuffix) part. A listing can be found at <u>https://www.diodes.com/products/automotive/automotiveproducts/</u>.
- This part is qualified to JEDEC standards (as references in AEC-Q) for High Reliability. https://www.diodes.com/quality/product-definitions/
- An Automotive-Compliant Part is Available Under Separate Datasheet (2N7002AQ)

### **Mechanical Data**

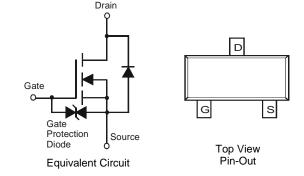
- Case: SOT23
- Case Material: Molded Plastic. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Annealed over Alloy 42 Leadframe. Solderable per MIL-STD-202, Method 208 3
- Terminal Connections: See Diagram
- Weight: 0.008 grams (Approximate)





Top View

SOT23



### Ordering Information (Note 4)

Part Number	Case	Packaging
2N7002A-7	SOT23	3,000/Tape & Reel
2N7002A-13	SOT23	10,000/Tape & Reel

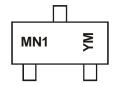
Notes: 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and

Lead-free. 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.



# **Marking Information**



MN1 = Product Type Marking Code YM = Date Code Marking Y or  $\overline{Y}$  = Year (ex: H = 2020) M or M = Month (ex: 9 = September)

### Date Code Key

Year	2008		2020	2021	2022	2023	2024	2025	2026	2027	2028	2029
Code	V		Н		J	К	L	М	N	0	Р	R
Month	Jan	Feb	Mar	Apr	Мау	Jun	Jul	Aug	Sep	Oct	Nov	Dec

# Maximum Ratings (@TA = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit	
Drain-Source Voltage		VDSS	60	V	
Gate-Source Voltage	V <sub>GSS</sub>	±20	V		
Continuous Drain Current (Note 5) $V_{GS} = 10V$ State $T_A =$		T <sub>A</sub> = +25°C T <sub>A</sub> = +85°C T <sub>A</sub> = +100°C	D	180 130 115	mA
Continuous Drain Current (Note 6) V <sub>GS</sub> = 10V	T <sub>A</sub> = +25°C T <sub>A</sub> = +85°C T <sub>A</sub> = +100°C	D	220 160 140	mA	
Maximum Continuous Body Diode Forward Currer	nt (Note 6)	ls	220	mA	
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1	%)		Ідм	800	mA

# Thermal Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit		
Total Dower Dissinction	(Note 5)	D-	370	mW	
Total Power Dissipation	(Note 6)	PD	540	TTIVV	
Thermal Desistance, Junction to Ambient	(Note 5)	Devi	348		
Thermal Resistance, Junction to Ambient	(Note 6)	Reja	241	°C/W	
Thermal Resistance, Junction to Case (N		Rejc	91		
Operating and Storage Temperature Range		TJ, TSTG	-55 to +150	°C	

Notes:

Device mounted on FR-4 PCB, with minimum recommended pad layout.
Device mounted on 1" x 1" FR-4 PCB with high coverage 2oz. Copper, single sided.

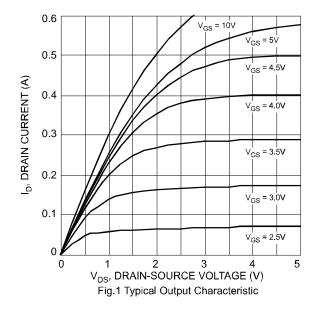


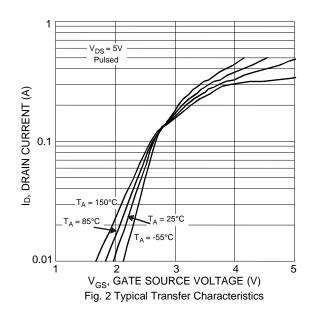
## Electrical Characteristics (@TA = +25°C, unless otherwise specified.)

				I _			
Characteristic		Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)							
Drain-Source Breakdown Voltage		BVDSS	60	70	—	V	$V_{GS} = 0V$ , $I_D = 10\mu A$
Zero Gate Voltage Drain Current		220	_	_	1.0 500	μA	$V_{DS} = 60V, V_{GS} = 0V$
Gate-Body Leakage	Gate-Body Leakage		_		±10	μA	$V_{GS} = \pm 20V, V_{DS} = 0V$
ON CHARACTERISTICS (Note 7)							
Gate Threshold Voltage		VGS(TH)	1.2	_	2.0	V	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250µA
Static Drain-Source On-Resistance	@ T <sub>J</sub> = +25°C			3.5	6	0	V <sub>GS</sub> = 5.0V, I <sub>D</sub> = 0.115A
	@ TJ = +125°C		_	3.0	5	Ω	V <sub>GS</sub> = 10V, I <sub>D</sub> = 0.115A
Forward Transconductance		<b>g</b> fs	80		_	mS	V <sub>DS</sub> = 10V, I <sub>D</sub> = 0.115A
DYNAMIC CHARACTERISTICS (Note	e 8)			•	•	•	·
Input Capacitance		Ciss	_	23	_	pF	
Output Capacitance		Coss	_	3.4	_	pF	V <sub>DS</sub> = 25V, V <sub>GS</sub> = 0V, f = 1.0MHz
Reverse Transfer Capacitance		Crss	_	1.4		pF	1
Gate Resistance		R <sub>G</sub>	_	260	400	Ω	$V_{DS} = 0V, V_{GS} = 0V, f = 1.0MHz$
SWITCHING CHARACTERISTICS (N	ote 8)	•		•	•	•	
Turn-On Delay Time		tD(ON)	_	10		ns	$V_{DD} = 30V, I_D = 0.115A, R_L = 150\Omega,$
Turn-Off Delay Time		tD(OFF)	_	33	_	ns	$V_{GEN} = 10V, R_{GEN} = 25\Omega$

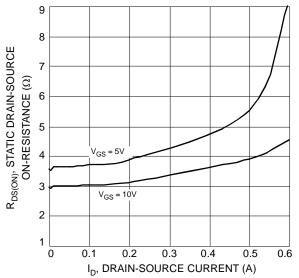
Notes:

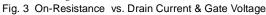
Short duration pulse test used to minimize self-heating effect.
Guaranteed by design. Not subject to product testing.

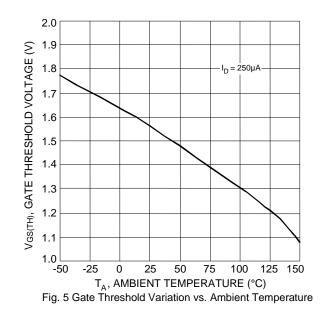


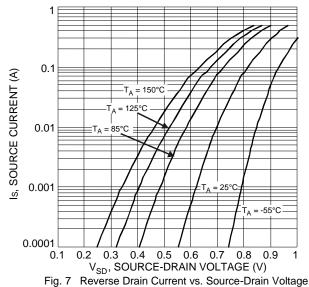


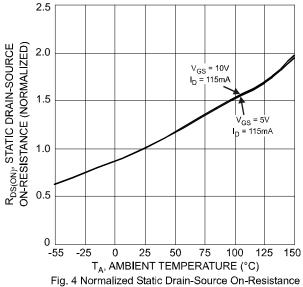




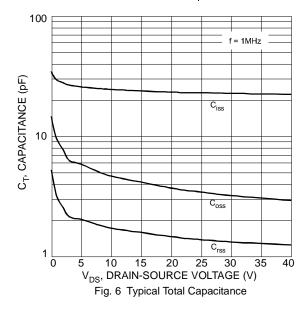








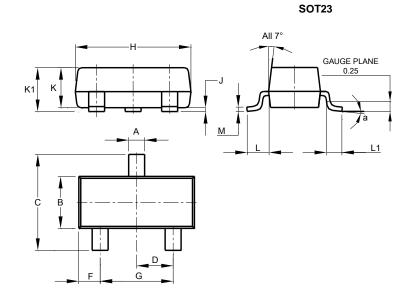






## **Package Outline Dimensions**

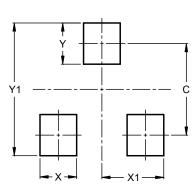
Please see http://www.diodes.com/package-outlines.html for the latest version.



	SOT23							
Dim	Min	Max	Тур					
Α	0.37	0.51	0.40					
в	1.20	1.40	1.30					
С	2.30	2.50	2.40					
D	0.89	1.03	0.915					
F	0.45	0.60	0.535					
G	1.78	2.05	1.83					
н	2.80	3.00	2.90					
J	0.013	0.10	0.05					
К	0.890	1.00	0.975					
K1	0.903	1.10	1.025					
L	0.45	0.61	0.55					
L1	0.25	0.55	0.40					
М	0.085	0.150	0.110					
а	0°	8°						
All	Dimens	ions in	mm					

### **Suggested Pad Layout**

Please see http://www.diodes.com/package-outlines.html for the latest version.



SOT23

Dimensions	Value (in mm)
С	2.0
Х	0.8
X1	1.35
Y	0.9
Y1	2.9

2N7002A Document number: DS31360 Rev. 14 - 2



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